# **DRC3144V**

### Silicon NPN epitaxial planar type

For digital circuits Complementary to DRA3144V DRC9144V in SSSMini3 type package

#### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

#### Packaging

Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V
Collector current	$I_{C}$	100	mA
Total power dissipation	P <sub>T</sub>	100	mW
Junction temperature	$T_j$	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

#### ■ Package

• Code

SSSMini3-F2-B

Pin Name

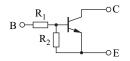
1: Base

2: Emitter

3: Collector

### ■ Marking Symbol: NJ

#### ■ Internal Connection



Resistance	R <sub>1</sub>	47	kΩ
value	R <sub>2</sub>	10	kΩ

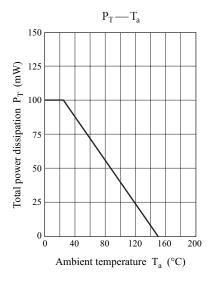
### ■ Electrical Characteristics $T_a = 25$ °C±3°C

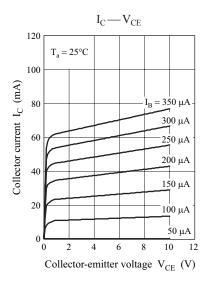
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu A, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_{C} = 0$			0.2	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	30			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	6.3			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 100  \mu\text{A}$			1.9	V
Input resistance	$R_1$		-30%	47	+30%	kΩ
Resistance ratio	$R_1/R_2$		3.7	4.7	5.7	

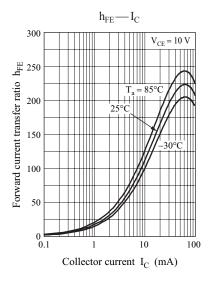
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

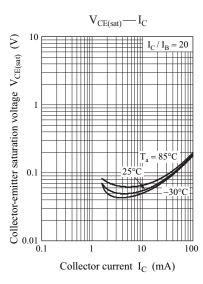
DRC3144V

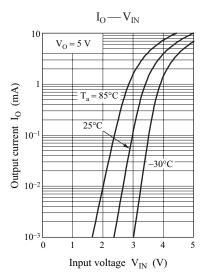
## **Panasonic**

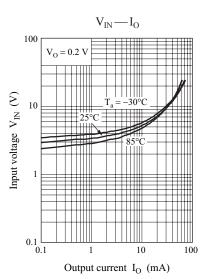








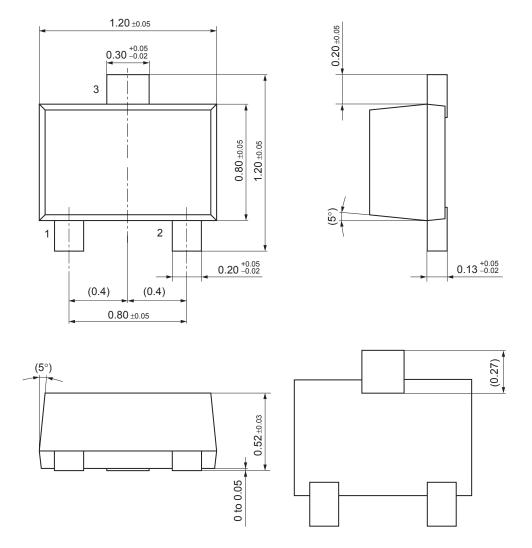




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# SSSMini3-F2-B

Unit: mm



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